

Federico Panciera

List of Publications by Year in descending order

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24
papers

847
citations

623574

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25
docs citations

25
times ranked

1182
citing authors

#	ARTICLE	IF	CITATIONS
1	Statistics of Nucleation and Growth of Single Monolayers in Nanowires: Towards a Deterministic Regime. <i>Physica Status Solidi - Rapid Research Letters</i> , 2022, 16, .	1.2	8
2	Regulated Dynamics with Two Monolayer Steps in Vapor-Solid Growth of Nanowires. <i>ACS Nano</i> , 2022, 16, 4397-4407.	7.3	5
3	Band-Gap Landscape Engineering in Large-Scale 2D Semiconductor van der Waals Heterostructures. <i>ACS Nano</i> , 2021, 15, 7279-7289.	7.3	28
4	Nucleation and lateral growth kinetics of the NiSi phase at the epitaxial $\hat{1}$ -Ni ₂ Si/Si interface. <i>Acta Materialia</i> , 2020, 198, 100-110.	3.8	7
5	Phase Selection in Self-catalyzed GaAs Nanowires. <i>Nano Letters</i> , 2020, 20, 1669-1675.	4.5	83
6	In situ TEM modification of individual silicon nanowires and their charge transport mechanisms. <i>Nanotechnology</i> , 2020, 31, 494002.	1.3	3
7	Growth Dynamics of Gallium Nanodroplets Driven by Thermally Activated Surface Diffusion. <i>Journal of Physical Chemistry Letters</i> , 2019, 10, 5082-5089.	2.1	3
8	Selective Wet Etching of Silicon Germanium in Composite Vertical Nanowires. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 36839-36846.	4.0	24
9	Surface Crystallization of Liquid Au-Si and Its Impact on Catalysis. <i>Advanced Materials</i> , 2019, 31, 1806544.	11.1	23
10	Atomic Step Flow on a Nanofacet. <i>Physical Review Letters</i> , 2018, 121, 166101.	2.9	113
11	Growth Dynamics of Ga Nanodroplets on 2D Substrate. <i>Microscopy and Microanalysis</i> , 2018, 24, 264-265.	0.2	0
12	Controlling nanowire growth through electric field-induced deformation of the catalyst droplet. <i>Nature Communications</i> , 2016, 7, 12271.	5.8	49
13	Interface dynamics and crystal phase switching in GaAs nanowires. <i>Nature</i> , 2016, 531, 317-322.	13.7	272
14	Nanowire growth kinetics in aberration corrected environmental transmission electron microscopy. <i>Chemical Communications</i> , 2016, 52, 5686-5689.	2.2	20
15	Synthesis of nanostructures in nanowires using sequential catalyst reactions. <i>Nature Materials</i> , 2015, 14, 820-825.	13.3	82
16	Creating New VLS Silicon Nanowire Contact Geometries by Controlling Catalyst Migration. <i>Nano Letters</i> , 2015, 15, 6535-6541.	4.5	16
17	Ni(Pt)-silicide contacts on CMOS devices: Impact of substrate nature and Pt concentration on the phase formation. <i>Microelectronic Engineering</i> , 2014, 120, 34-40.	1.1	10
18	Direct epitaxial growth of $\hat{1}$ -Ni ₂ Si by reaction of a thin Ni(10at.% Pt) film with Si(100) substrate. <i>Scripta Materialia</i> , 2014, 78-79, 9-12.	2.6	22

#	ARTICLE	IF	CITATIONS
19	Atom probe tomography for advanced metallization. <i>Microelectronic Engineering</i> , 2014, 120, 19-33.	1.1	18
20	Atom probe tomography of SRAM transistors: Specimen preparation methods and analysis. <i>Microelectronic Engineering</i> , 2013, 107, 167-172.	1.1	23
21	Pt redistribution in N-MOS transistors during Ni salicide process. <i>Microelectronic Engineering</i> , 2013, 107, 173-177.	1.1	15
22	Three-dimensional distribution of Al in high- <i>k</i> metal gate: Impact on transistor voltage threshold. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	12
23	Evaluation and modeling of lanthanum diffusion in TiN/La ₂ O ₃ /HfSiON/SiO ₂ /Si high- <i>k</i> stacks. <i>Applied Physics Letters</i> , 2012, 101, 182901.	1.5	11
24	Growth-Related Formation Mechanism of I ₃ -Type Basal Stacking Fault in Epitaxially Grown Hexagonal Ge ₂ H. <i>Advanced Materials Interfaces</i> , 0, , 2102340.	1.9	0